



## 512K x 32 SRAM MODULE

### PUMA 2/77S16000/A/B - 020/025/35

Elm Road, West Chirton, NORTH SHIELDS, Tyne & Wear  
NE29 8SE, England Tel. +44 (0191) 2930500 Fax. +44 (0191) 2590997

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#### Description

Available in PGA (PUMA 2) and Gullwing (PUMA 77) footprints, the PUMA \*\*S16000 is a 16 MBit SRAM module user configurable as 512K x 32, 1M x 16 or 2M x 8. The device is available with fast access times of 20,25 and 35ns. The device may be screened in accordance with MIL-STD-883.

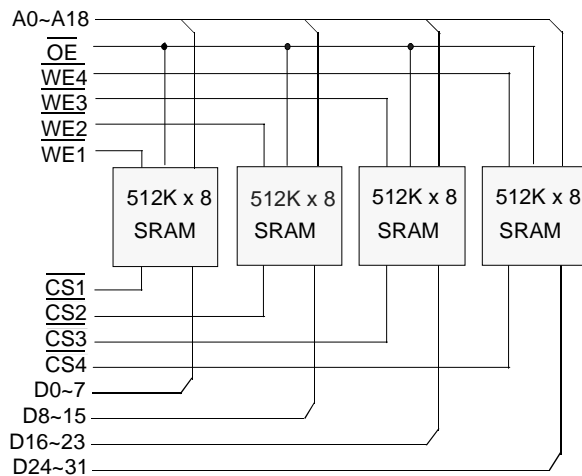
16,777,216 bit CMOS High Speed Static RAM

#### Features

- 16MBit Fast SRAM Module.
- Fast Access times of 20/25/35ns.
- Configurable as 8 / 16 / 32 bit wide output.
- Operating Power 1980 / 2640 / 3960 mW (max).  
Standby TTL 1320mW (max).
- Single 5V±10% Power supply.
- TTL compatible inputs and outputs.
- May be screened in accordance with MIL-STD-883.
- PUMA 2 - 66 pin ceramic PGA
- PUMA77 - 68 pin ceramic Gullwing

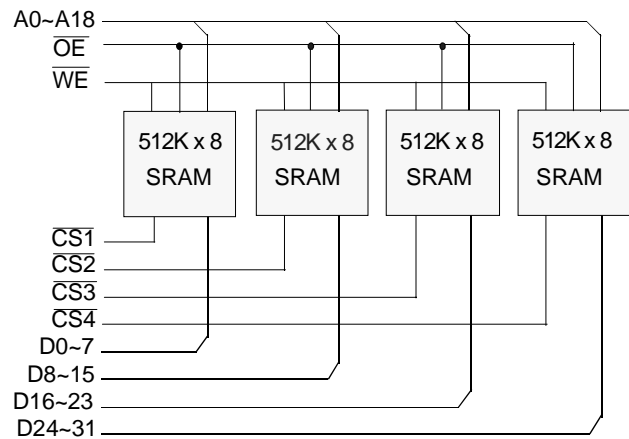
#### Block Diagram

PUMA 2S16000 and 77S16000A, 77S16000B



#### Block Diagram

PUMA 77S16000



#### Pin Functions

**A0~A18** Address Inputs  
**CS1~4** Chip Select  
**WE1~4** Write Enable  
**V<sub>cc</sub>** Power (+5V)

**D0~D31** Data Inputs/Outputs  
**OE** Output Enable  
**NC** No Connect  
**GND** Ground

**DC OPERATING CONDITIONS****Absolute Maximum Ratings**<sup>(1)</sup>

Voltage on any pin relative to $V_{SS}$ <sup>(2)</sup>	$V_T$	-0.5V to +7.0	V
Power Dissipation	$P_D$	4	W
Storage Temperature	$T_{STG}$	-55 to +150	°C

Notes (1) Stresses above those listed may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**Recommended Operating Conditions**

Parameter	Symbol	min	typ	max	units
Supply Voltage	$V_{CC}$	4.5	5.0	5.5	V
Input High Voltage	$V_{IH}$	2.2	-	$V_{CC}+0.5$	V
Input Low Voltage	$V_{IL}$	-0.5	-	0.8	V
Operating Temperature	$T_A$	0	-	70	°C
	$T_{AI}$	-40	-	85	°C (Suffix I)
	$T_{AM}$	-55	-	125	°C (Suffix M, MB)

Parameter	Symbol	Test Condition	min	typ <sup>(1)</sup>	max	Unit
Input Leakage Current	Address, $\overline{OE}$	$I_{L1}$	$V_{IN} = 0V$ to $V_{CC}$	-8	-	8 $\mu A$
	$\overline{WE}$ , $\overline{CS}$	$I_{L2}$	$V_{IN} = 0V$ to $V_{CC}$	-2	-	2 $\mu A$
Output Leakage Current		$I_{LO}$	$\overline{CS}^{(2)} = V_{IH}$ or $\overline{OE} = V_{IH}$ , $V_{IO} = 0V$ to $V_{CC}$	-8	-	8 $\mu A$
Average Supply Current	32 bit	$I_{CC32}$	$\overline{WE}^{(2)} = V_{IL}$	-	-	720 mA
			$\overline{CS}^{(2)} = V_{IL}$ , Minimum cycle, $I_{IO} = 0mA$	-	-	480 mA
	16 bit	$I_{CC16}$	As above	-	-	360 mA
	8 bit	$I_{CC8}$	As above	-	-	240 mA
Standby Supply Current	TTL levels	$I_{SB}$	$\overline{CS}^{(2)} = V_{IH}$ , $V_{CC} = 5.5V$	-	-	240 mA
Output Voltage Low		$V_{OL}$	$I_{OL} = 8.0 mA$	-	-	0.4 V
Output Voltage High		$V_{OH}$	$I_{OH} = -4.0 mA$	2.4	-	- V

Notes: (1) Typical values are at  $V_{CC} = 5.0V$ ,  $T_A = 25^\circ C$  and specified loading.

(2)  $\overline{CS}$  and  $\overline{WE}$  above are accessed through  $\overline{CS}1\sim4$  and  $\overline{WE}1\sim4$  respectively. These inputs must be operated simultaneously for 32 bit mode, in pairs for 16 bit mode and singly for 8 bit mode.

**Capacitance** ( $V_{CC}=5V\pm 10\%$ ,  $T_A=25^\circ C$ ) Note: These parameters are calculated and not measured.

Parameter	Symbol	Test Condition	typ	max	Unit
Input Capacitance Address, $\overline{OE}$	$C_{IN1}$	$V_{IN}=0V$	-	34	pF
	$C_{IN2}$	$V_{IN}=0V$	-	6	pF
I/O Capacitance	$C_{I/O}$	$V_{I/O}=0V$	-	42	pF (8 bit mode)

### Operating Modes

The Table below shows the logic inputs required to control the operating modes of each of the SRAMs on the device.

Mode	$\overline{CS}$	$\overline{OE}$	$\overline{WE}$	$V_{CC}$ Current	I/O Pin	Reference Cycle
Not Selected	1	X	X	$I_{SB1}, I_{SB2}$	High Z	Power Down
Output Disable	0	1	1	$I_{CC}$	High Z	
Read	0	0	1	$I_{CC}$	$D_{OUT}$	Read cycle
Write	0	X	0	$I_{CC}$	$D_{IN}$	Write Cycle

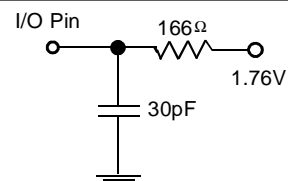
1 =  $V_{IH}$ ,  
 0 =  $V_{IL}$ ,  
 X = Don't Care

Note:  $\overline{CS}$  above is accessed through  $\overline{CS1}\sim\overline{4}$  and  $\overline{WE}$  is accessed through  $\overline{WE1}\sim\overline{4}$ . For correct operation,  $\overline{CS1}\sim\overline{4}$  and  $\overline{WE1}\sim\overline{4}$  must operate simultaneously for 32 bit operation, in pairs for 16 bit operation, or singly for 8 bit operation.

### AC Test Conditions

- \*Input pulse levels: 0.0V to 3.0V
- \*Input rise and fall times: 3 ns
- \*Input and Output timing reference levels: 1.5V
- \* $V_{CC}=5V\pm 10\%$
- \*PUMA module is tested in 32 bit mode.

### Output Load



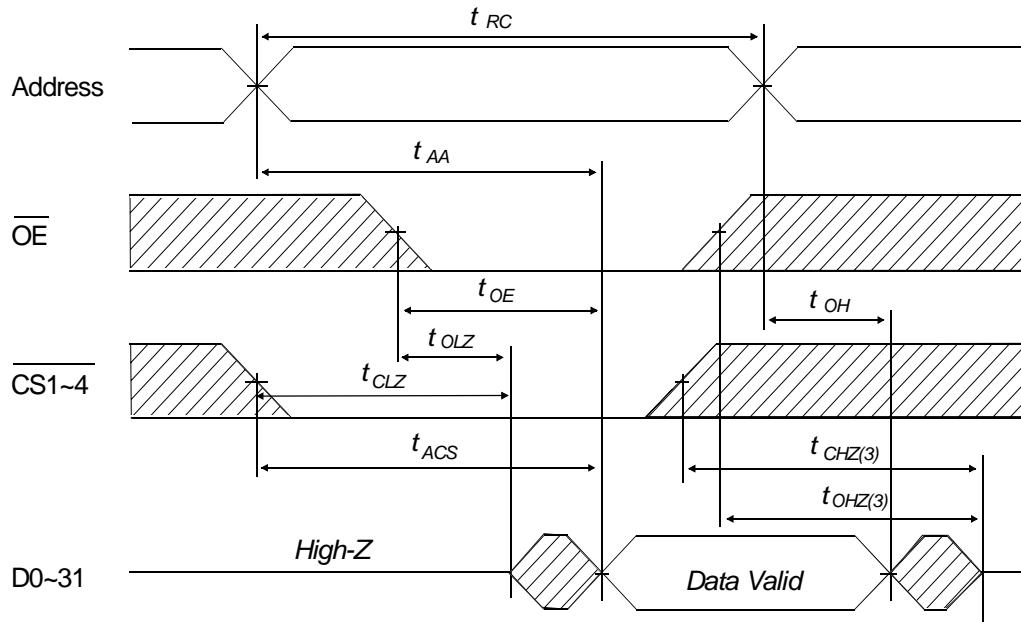
**AC OPERATING CONDITIONS****Read Cycle**

<i>Parameter</i>	<i>Symbol</i>	<i>020</i>		<i>025</i>		<i>35</i>		<i>Units</i>
		<i>min</i>	<i>max</i>	<i>min</i>	<i>max</i>	<i>min</i>	<i>max</i>	
Read Cycle Time	$t_{RC}$	20	-	25	-	35	-	ns
Address Access Time	$t_{AA}$	-	20	-	25	-	35	ns
Chip Select Access Time	$t_{ACS}$	-	20	-	25	-	35	ns
Output Enable to Output Valid	$t_{OE}$	-	10	-	15	-	15	ns
Output Hold from Address Change	$t_{OH}$	5	-	5	-	5	-	ns
Chip Selection to Output in Low Z	$t_{CLZ}$	5	-	5	-	5	-	ns
Output Enable to Output in Low Z	$t_{OLZ}$	5	-	0	-	0	-	ns
Chip Deselection to Output in High Z <sup>(3)</sup>	$t_{CHZ}$	-	10	0	10	0	10	ns
Output Disable to Output in High Z <sup>(3)</sup>	$t_{OHZ}$	0	10	0	10	0	10	ns

**Write Cycle**

<i>Parameter</i>	<i>Symbol</i>	<i>020</i>		<i>025</i>		<i>35</i>		<i>Unit</i>
		<i>min</i>	<i>max</i>	<i>min</i>	<i>max</i>	<i>min</i>	<i>max</i>	
Write Cycle Time	$t_{WC}$	20	-	25	-	35	-	ns
Chip Selection to End of Write	$t_{CW}$	15	-	15	-	15	-	ns
Address Valid to End of Write	$t_{AW}$	15	-	15	-	15	-	ns
Address Setup Time	$t_{AS}$	0	-	0	-	0	-	ns
Write Pulse Width	$t_{WP}$	15	-	15	-	15	-	ns
Write Recovery Time	$t_{WR}$	0	-	0	-	0	-	ns
Write to Output in High Z	$t_{WHZ}$	0	10	0	10	0	10	ns
Data to Write Time Overlap	$t_{DW}$	10	-	10	-	10	-	ns
Data Hold from Write Time	$t_{DH}$	0	-	0	-	0	-	ns
Output Active from End of Write	$t_{OW}$	5	-	5	-	5	-	ns

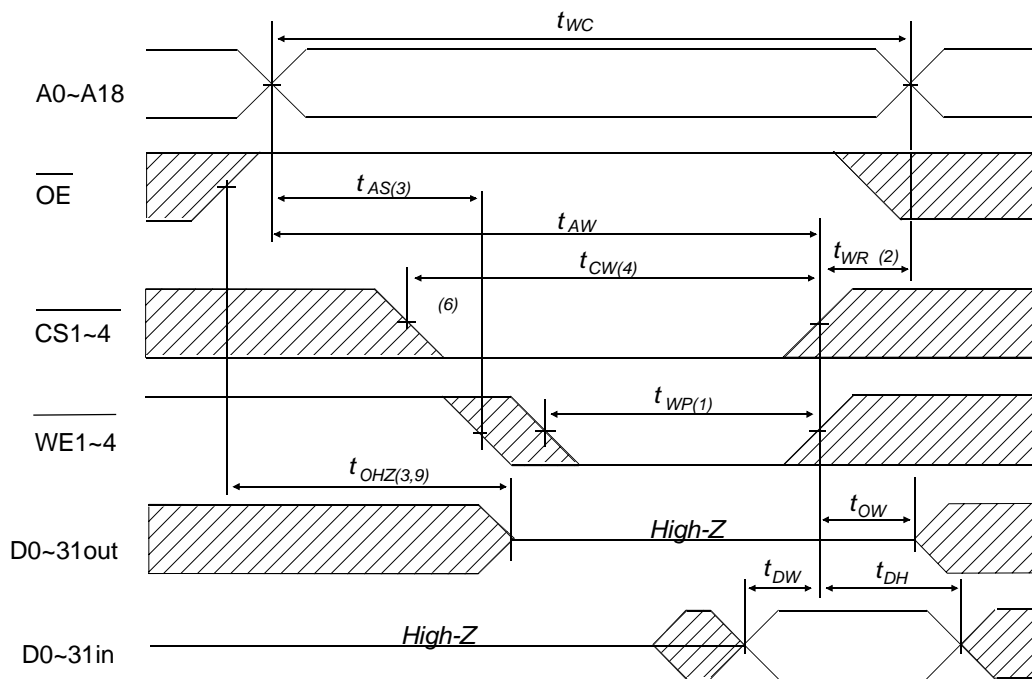
**Read Cycle Timing Waveform<sup>(1,2)</sup>**



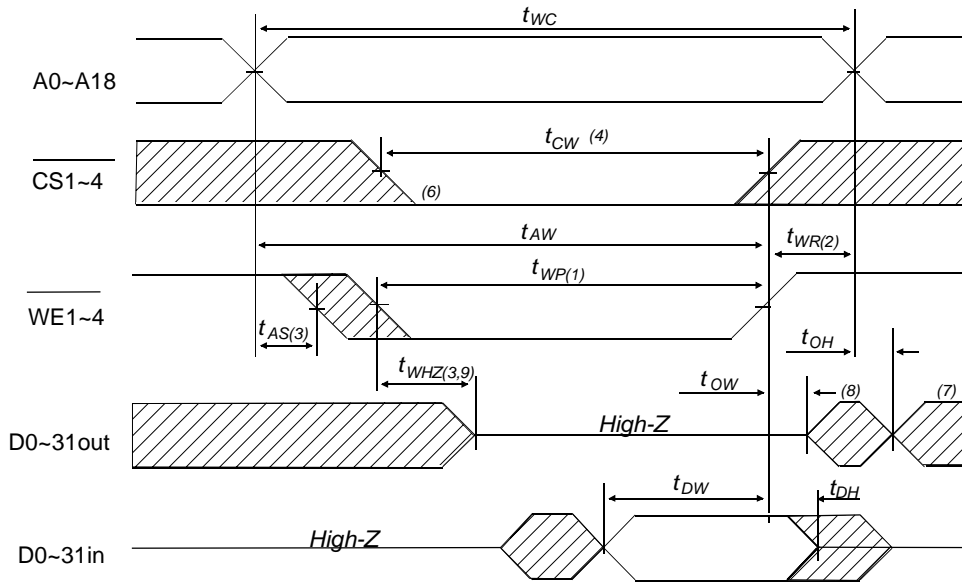
Notes:

- (1) During the Read Cycle,  $\overline{WE}$  is high for the module.
- (2) Address valid prior to or coincident with  $\overline{CS}$  transition Low.
- (3)  $t_{CHZ}$  and  $t_{OHZ}$  are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels. These parameters are sampled and not 100% tested.

**Write Cycle No.1 Timing Waveform**



**Write Cycle No.2 Timing Waveform <sup>(5)</sup>**

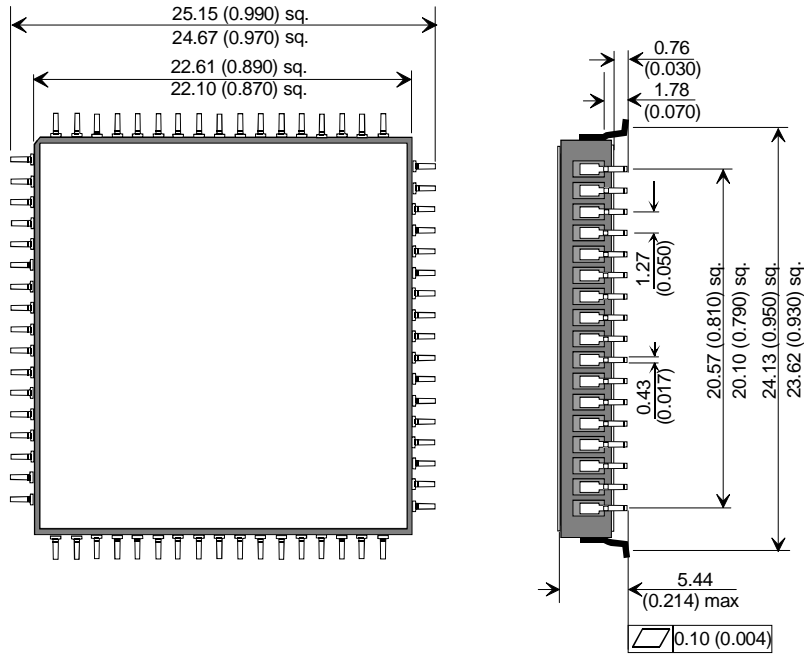


**AC Characteristics Notes**

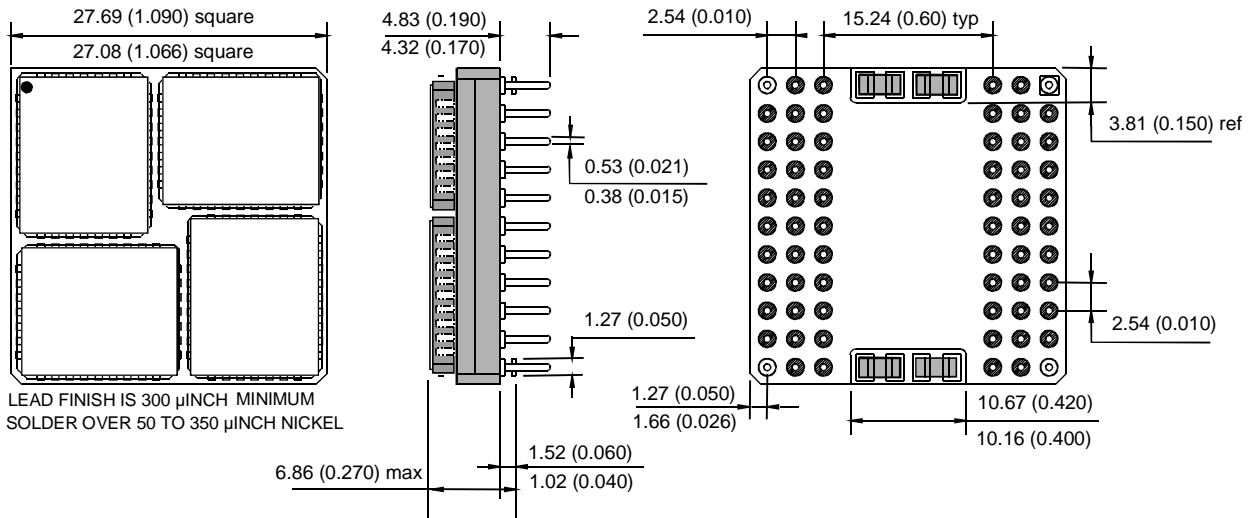
- (1) A write occurs during the overlap ( $t_{WP}$ ) of a low  $\overline{CS}$  and a low  $\overline{WE}$ .
- (2)  $t_{WR}$  is measured from the earlier of  $\overline{CS}$  or  $\overline{WE}$  going high to the end of write cycle.
- (3) During this period, I/O pins are in the output state. Input signals out of phase must not be applied.
- (4) If the  $\overline{CS}$  low transition occurs simultaneously with the  $\overline{WE}$  low transition or after the  $\overline{WE}$  low transition, outputs remain in a high impedance state.
- (5)  $\overline{OE}$  is continuously low. ( $\overline{OE}=V_{IL}$ )
- (6)  $D_{OUT}$  is in the same phase as written data of this write cycle.
- (7)  $D_{OUT}$  is the read data of next address.
- (8) If  $\overline{CS}$  is low during this period, I/O pins are in the output state. Input signals out of phase must not be applied.
- (9)  $t_{WHZ}$  and  $t_{OHZ}$  are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels. These parameters are sampled and not 100% tested.

**Package Details**

**PUMA 77S16000**

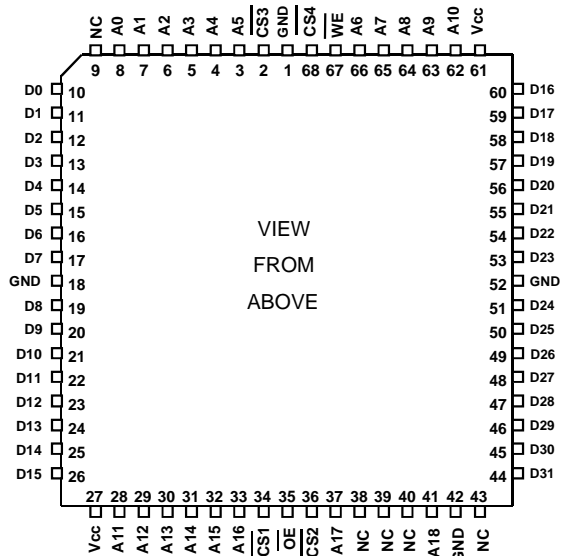


**PUMA 2S16000**

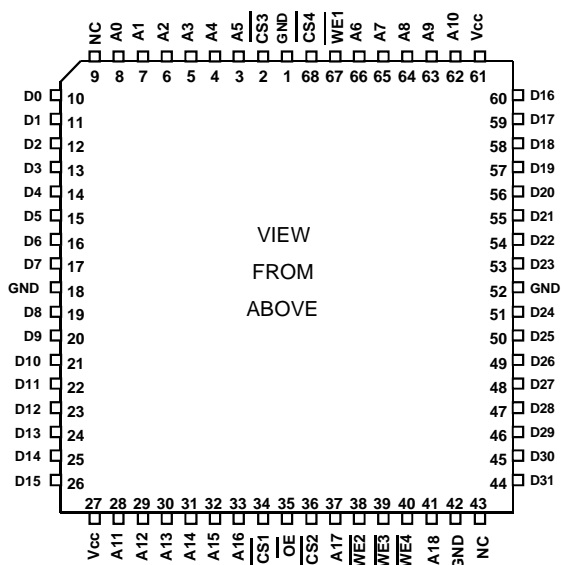


# Pin Definitions

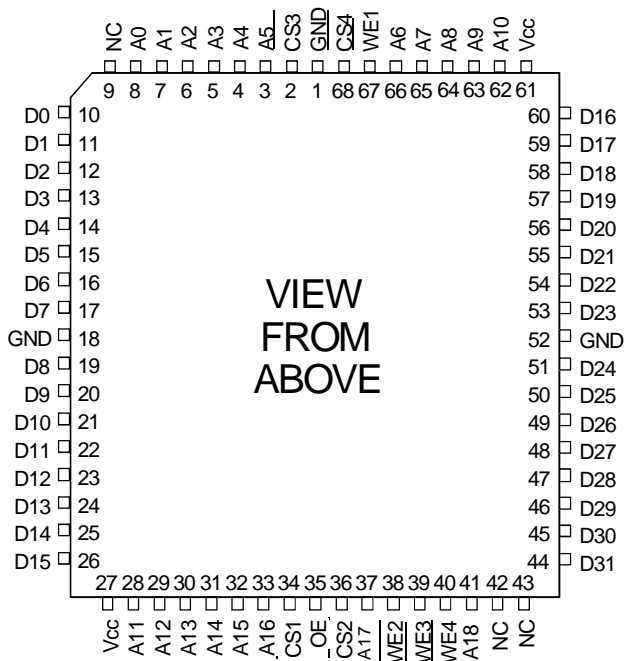
PUMA 77S16000



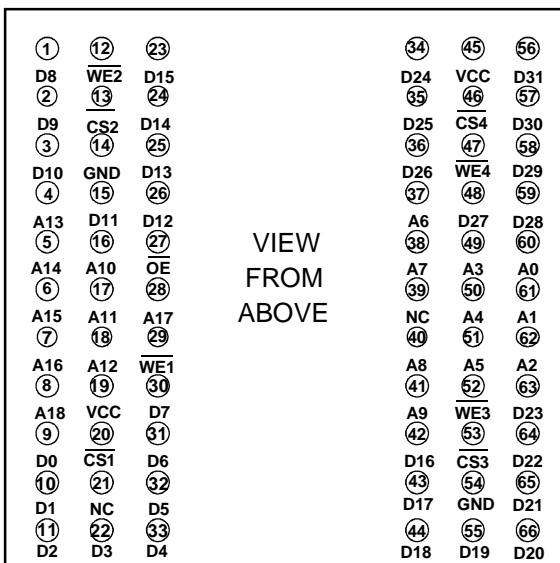
PUMA 77S16000A



PUMA 77S16000B



PUMA 2S16000





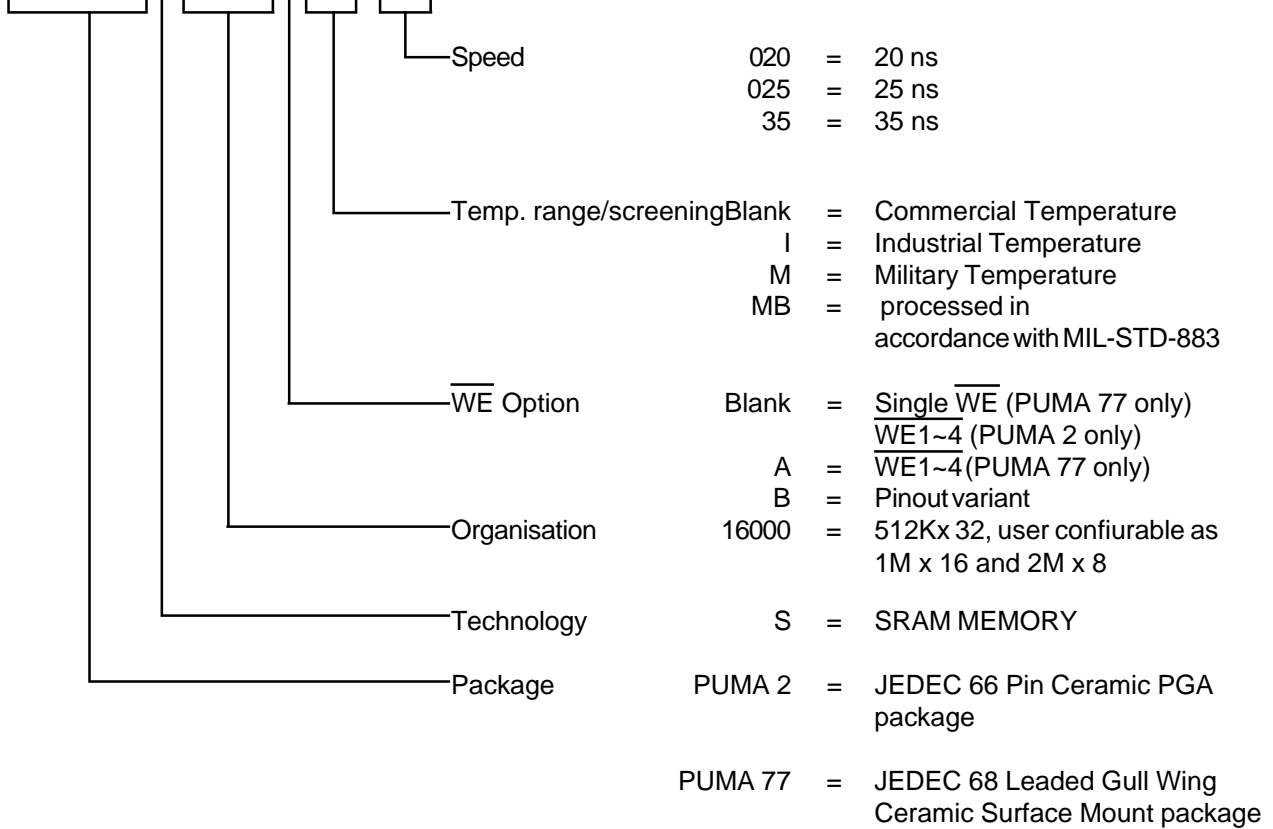
**Military Screening Procedure**

**MultiChip Screening Flow** for high reliability product in accordance with Mil-883 method 5004 shown below

<b>MB MULTICHIP MODULE SCREENING FLOW</b>		
<b>SCREEN</b>	<b>TEST METHOD</b>	<b>LEVEL</b>
<b>Visual and Mechanical</b> Internal visual Temperature cycle Constant acceleration	2017 Condition B or manufacturers equivalent 1010 Condition B (10 Cycles,-55°C to +125°C) 2001 Condition E (Y <sub>1</sub> only) (10,000g)	100% 100% 100%
<b>Burn-In</b> Pre-Burn-in electrical Burn-in	Per applicable device specifications at T <sub>A</sub> =+25°C Method 1015,Condition D,T <sub>A</sub> =+125°C,160hrs min	100% 100%
<b>Final Electrical Tests</b> Static (dc)  Functional  Switching (ac)	Per applicable Device Specification a) @ T <sub>A</sub> =+25°C and power supply extremes b) @ temperature and power supply extremes  a) @ T <sub>A</sub> =+25°C and power supply extremes b) @ temperature and power supply extremes  a) @ T <sub>A</sub> =+25°C and power supply extremes b) @ temperature and power supply extremes	100% 100%  100% 100%  100% 100%
<b>Percent Defective allowable (PDA)</b>	Calculated at post burn-in at T <sub>A</sub> =+25°C	10%
<b>Hermeticity</b> Fine Gross	1014 Condition A Condition C	100% 100%
<b>Quality Conformance</b>	Per applicable Device Specification	Sample
<b>External Visual</b>	2009 Per vendor or customer specification	100%

**Ordering Information**

**PUMA 2S16000AMB-020**



Note :

Although this data is believed to be accurate, the information contained herein is not intended to and does not create any warranty of merchantability or fitness for a particular purpose.

Our products are subject to a constant process of development. Data may be changed at any time without notice.

Products are not authorised for use as critical components in life support devices without the express written approval of a company director.